



FETek Technology Corp.

FKH15810C

N-Ch 100V Fast Switching MOSFETs

General Description

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low $R_{DS(ON)}$
- ★ Advanced high cell density Trench technology

Applications

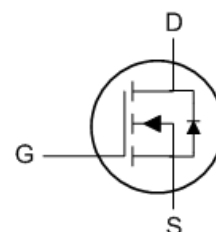
- ★ MOTOR Driver.
- ★ BMS.
- ★ High frequency switching and synchronous rectification.

Product Summary



BVDSS	RDSON	ID
100V	4.5mΩ	120A

TO263 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	120	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	100	A
I_{DM}	Pulsed Drain Current ²	480	A
EAS	Single Pulse Avalanche Energy ³	196	mJ
I_{AS}	Avalanche Current	28	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	227	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.5	$^{\circ}C/W$

**Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)**

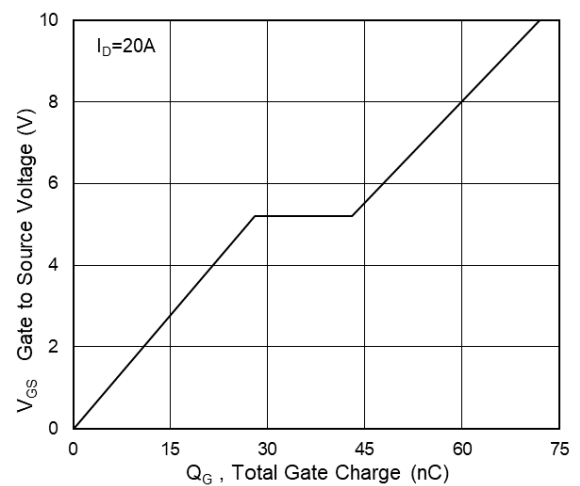
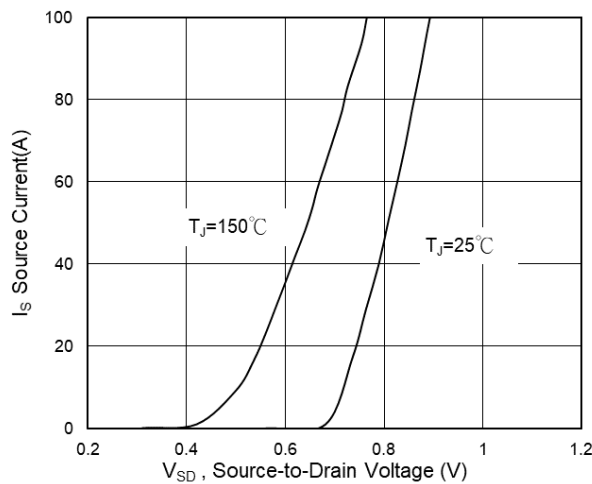
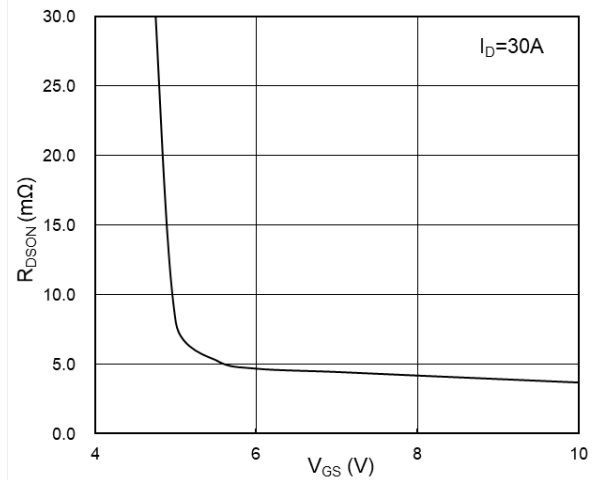
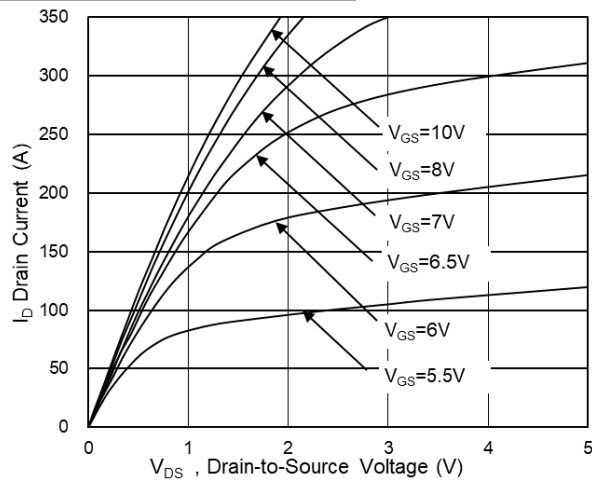
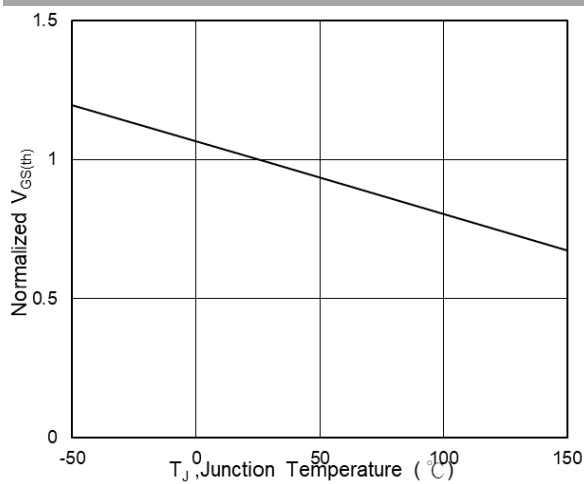
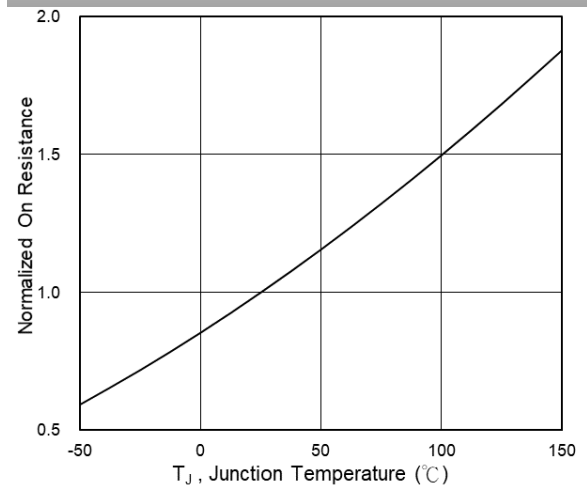
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=30A$	---	3.7	4.5	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	2.0	3.0	4.0	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=100V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=100V$, $V_{GS}=0V$, $T_J=125^\circ\text{C}$	---	---	10	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=30A$	---	50	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	1	---	Ω
Q_g	Total Gate Charge (10V)	$V_{DS}=50V$, $V_{GS}=10V$, $I_D=20A$	---	72	---	nC
Q_{gs}	Gate-Source Charge		---	28	---	
Q_{gd}	Gate-Drain Charge		---	15	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V$, $V_{GS}=10V$, $R_G=3.0\Omega$, $I_D=20A$	---	35	---	ns
T_r	Rise Time		---	18	---	
$T_{d(off)}$	Turn-Off Delay Time		---	45	---	
T_f	Fall Time		---	55	---	
C_{iss}	Input Capacitance	$V_{DS}=50V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	4725	---	pF
C_{oss}	Output Capacitance		---	609	---	
C_{rss}	Reverse Transfer Capacitance		---	14	---	

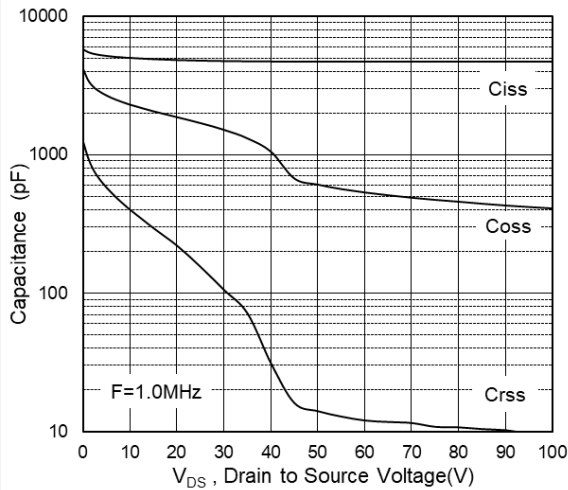
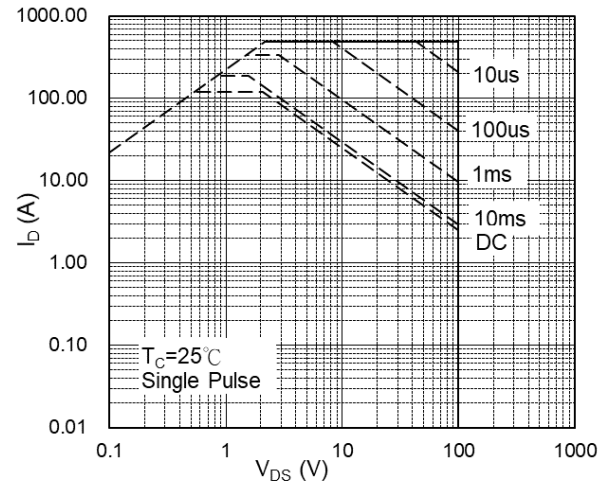
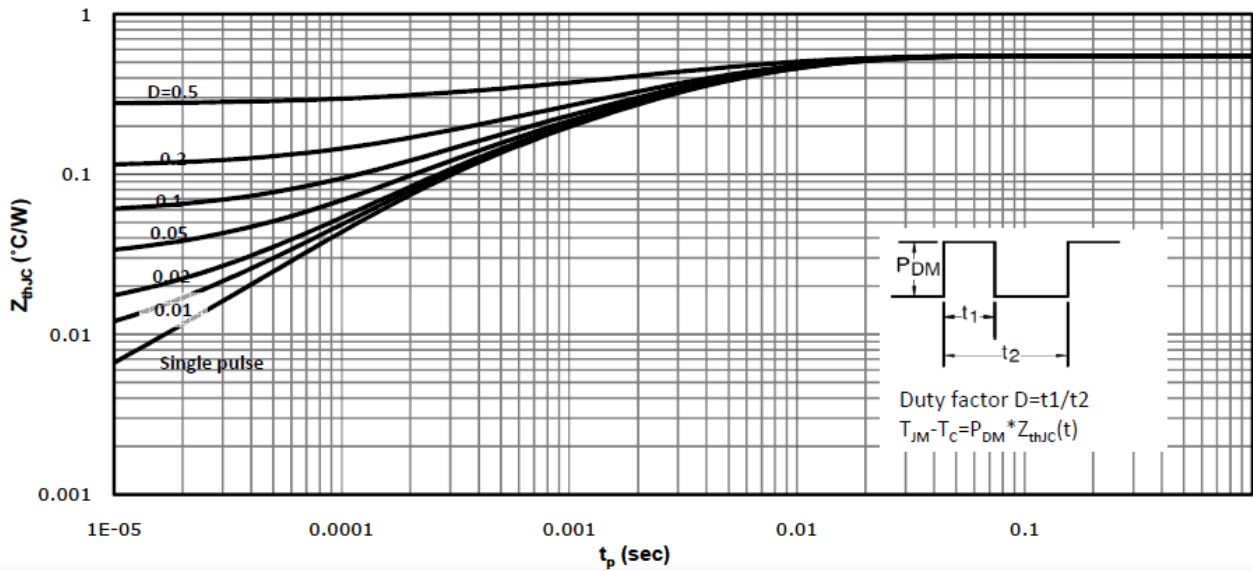
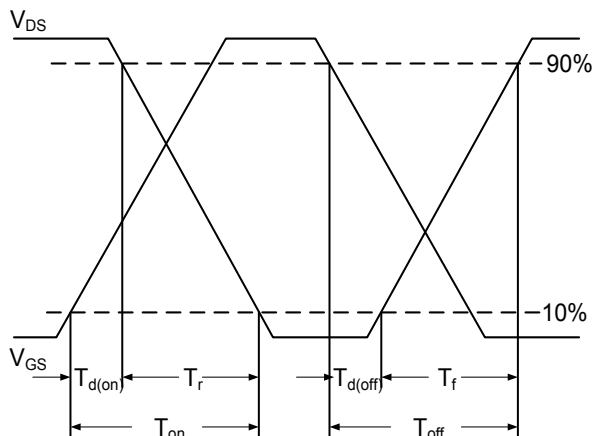
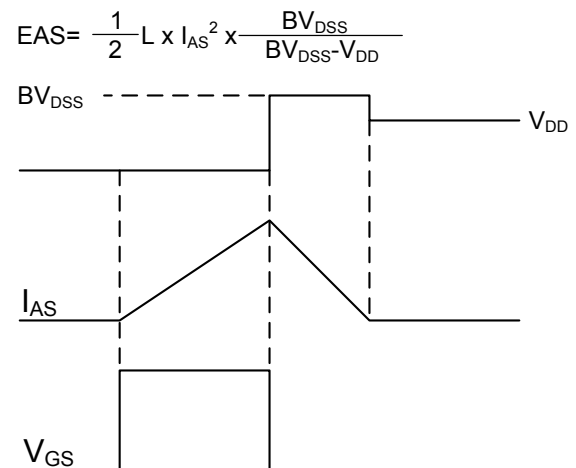
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	120	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=50A$, $T_J=25^\circ\text{C}$	---	---	1.3	V
t_{rr}	Reverse Recovery Time	$I_F=30A$, $dI/dt=100A/\mu s$,	---	70	---	nS
Q_{rr}	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	170	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V$, $V_{GS}=10V$, $L=0.5mH$, $I_{AS}=28A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.
- 6.Package limitation current.

Typical Characteristics

Fig.3 Source Drain Forward Characteristics

Fig.4 Gate-Charge Characteristics



Fig.7 Capacitance

Fig.8 Safe Operating Area

Fig.9 Normalized Maximum Transient Thermal Impedance

Fig.10 Switching Time Waveform

Fig.11 Unclamped Inductive Switching Waveform